



National Semiconductor™

Discrete POWER & Signal Technologies

Pro Electron Bipolar Devices

Device No.	Case Style	V <sub>CES</sub> * V <sub>CEO</sub> (V) Min	V <sub>CE0</sub> (V) Min	V <sub>EB0</sub> (V) Min	I <sub>CB0</sub> V <sub>CB</sub> (nA) @ (V) Max	h <sub>FE</sub> h <sub>FE</sub> Min Max	I <sub>C</sub> & V <sub>CE</sub> (mA) (V) 1 1	V <sub>CE(SAT)</sub> (V) Max	V <sub>BE(SAT)</sub> V <sub>BE(ON)</sub> * (V) Min Max		I <sub>C</sub> (mA) Max	C <sub>ob</sub> (pF) Max	f <sub>T</sub> (MHz) Min Max	I <sub>C</sub> (mA) Max	NF (dB) Max	Test Conditions	Process No.
									I <sub>C</sub> @ (mA)	V <sub>CE</sub> (V)							
BC327	TO-92 (97)	50*	45	5	100* 45	40 100 600 1	300 1	0.7	1.2* 1.2*	500 300							67
BC327A	TO-92 (97)	60*	60	5	100* 45	40 100 400 1	300 1	0.7	1.2* 1.2*	300 500							67
BC327-16	TO-92 (97)	50*	45	5	100* 45	40 100 250 1	300 1	0.7	1.2* 1.2*	500 300							67
BC327-25	TO-92 (97)	50*	45	5	100* 45	40 160 400 1	300 1	0.7	1.2* 1.2*	500 300							67
BC328	TO-92 (97)	30*	25	5	100* 25	40 100 600 1	100 1	0.7	1.2 1.2	500 300							67
BC328-25	TO-92 (97)	30*	25	5	100* 25	40 160 400 1	100 1	0.7	1.2 1.2	500 300							67
BC337	TO-92 (97)	50*	45	5	100 20	40 100 600 1	100 1	0.7	0.7	500							12
BC337A	TO-92 (97)	60*	60	5	100 20	40 100 400 1	100 1	0.7	0.7	500							12
BC337-16	TO-92 (97)	50*	45	5	100 20	40 100 250 1	100 1	0.7	0.7	500							12
BC337-25	TO-92 (97)	50*	45	5	100 20	40 160 400 1	100 1	0.7	0.7	500							12
BC338	TO-92 (97)	30*	20	5	100 20	40 100 600 1	100 1	0.7	0.7	500							12
BC368	TO-92 (94)	25*	20	5	10K 25	50 85 375 60	5 10 500 1A	0.5	0.5	1A			40	10			37 (6-1)

NOTE: National preferred device for each process in bold. Number shown in parentheses indicates location (section-page) of device datasheet.